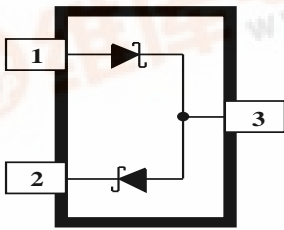


8920

DUAL SCHOTTKY DIODE



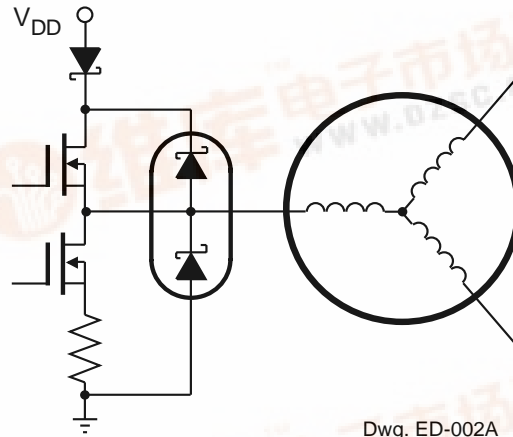
Dwg. PD-002

Schottky barrier diodes combine high rectification efficiency with high switching speeds and low series resistance. The A8920SLR dual diode is designed specifically for hard-disk drive applications requiring low voltage drop rectification of the spindle motor back-EMF during power-down head retraction. It is supplied in a 3-lead small-outline transistor package (SOT-23/TO-236AB) for surface-mounting for use over the operating temperature range of -20°C to $+85^{\circ}\text{C}$.

FEATURES

- Low Forward Voltage Drop 440 mV Typical at 150 mA
- 500 mA Forward Current
- 20 V Reverse Voltage

TYPICAL APPLICATION



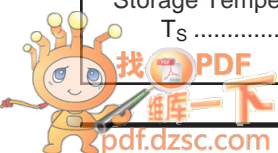
Dwg. ED-002A

ABSOLUTE MAXIMUM RATINGS

at $T_A = +25^{\circ}\text{C}$

Forward Current, I_F	500 mA
Reverse Voltage, V_R	20 V
Operating Temperature Range, T_A	-20°C to $+85^{\circ}\text{C}$
Storage Temperature Range, T_S	-65°C to $+150^{\circ}\text{C}$

Always order by complete part number: **A8920SLR**.

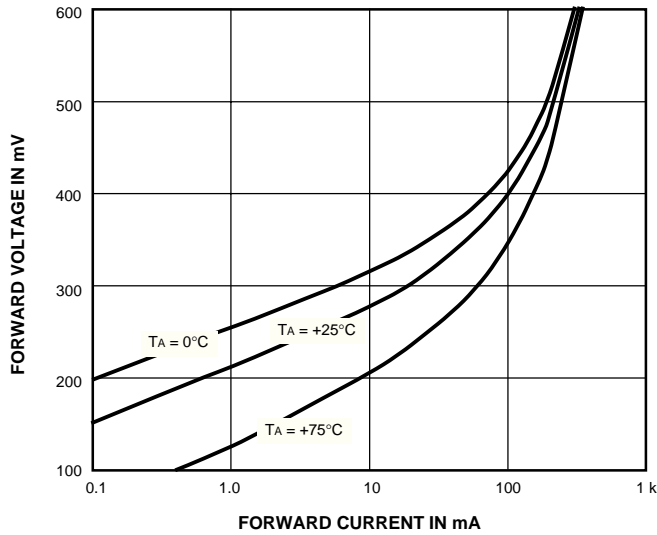


8920 DUAL SCHOTTKY DIODE

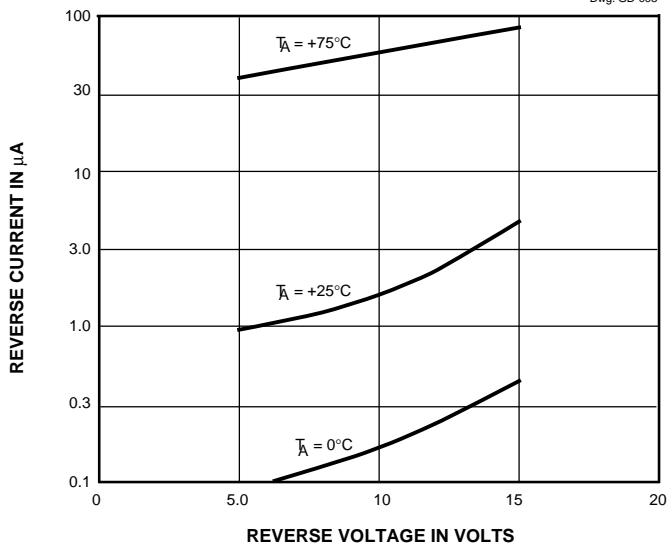
ELECTRICAL CHARACTERISTICS at $T_A = +25^\circ\text{C}$ (unless otherwise specified).

Characteristic	Symbol	Test Conditions	Limits			Units
			Min.	Typ.	Max.	
Reverse Breakdown Voltage	$V_{(BR)}$	$I_R = 100 \mu\text{A}$	20	—	—	V
Reverse Leakage Current	I_R	$V_R = 10 \text{ V}$	—	1.6	20	μA
Forward Voltage	V_F	$I_F = 50 \text{ mA}$	—	346	400	mV
		$I_F = 150 \text{ mA}$	—	440	500	mV
Junction Capacitance	C_T	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$	—	370	—	pF
Reverse Recovery Time	t_{rr}	$I_F = I_R = 100 \text{ mA}$	—	32	—	ns

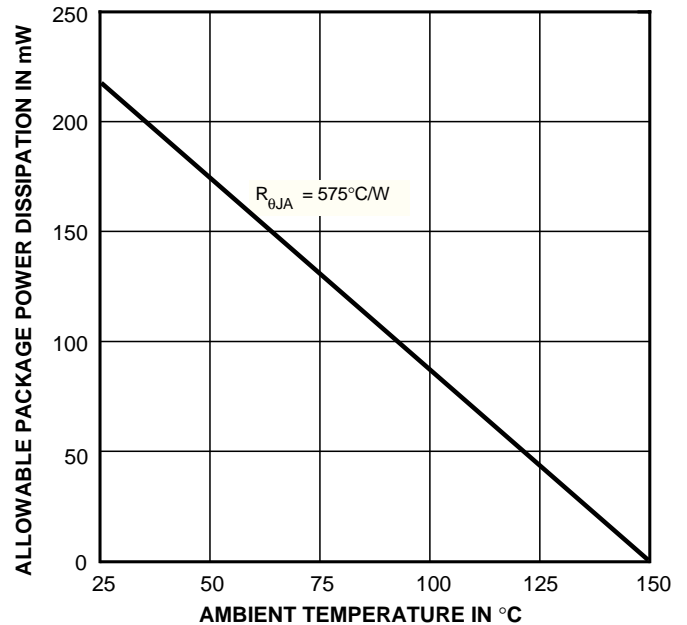
TYPICAL CHARACTERISTICS



Dwg. GD-003



Dwg. GD-004



Dwg. GD-002

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